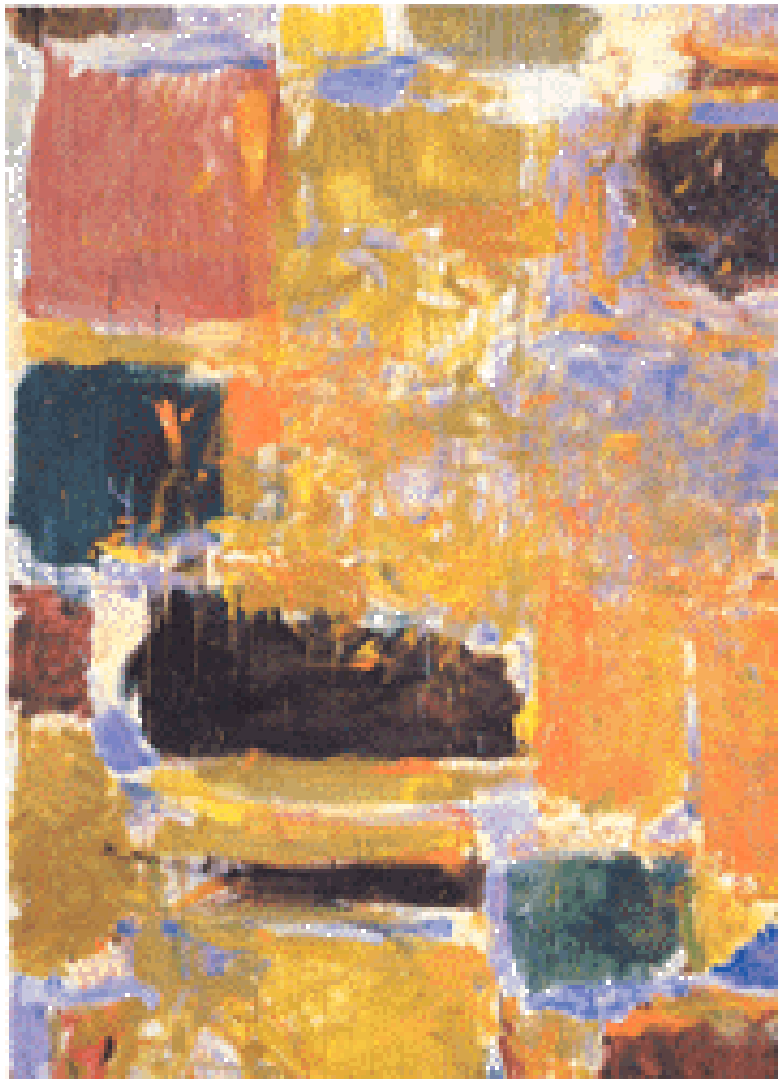

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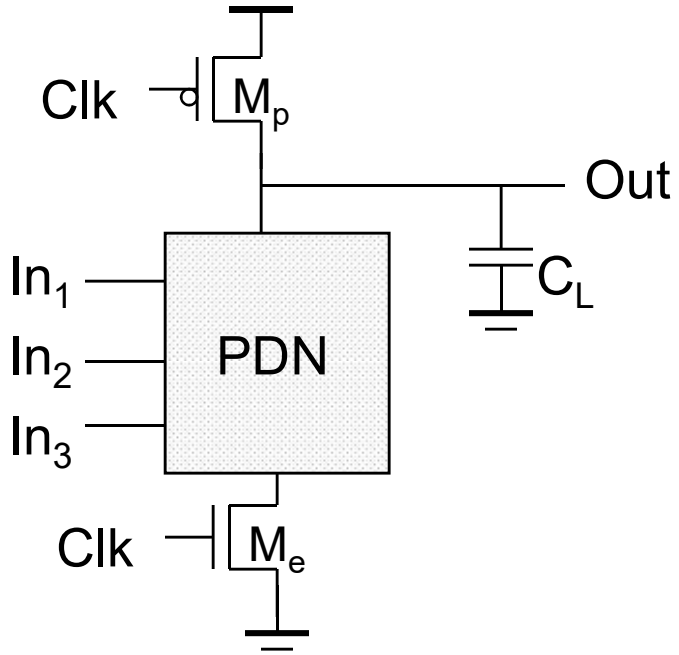

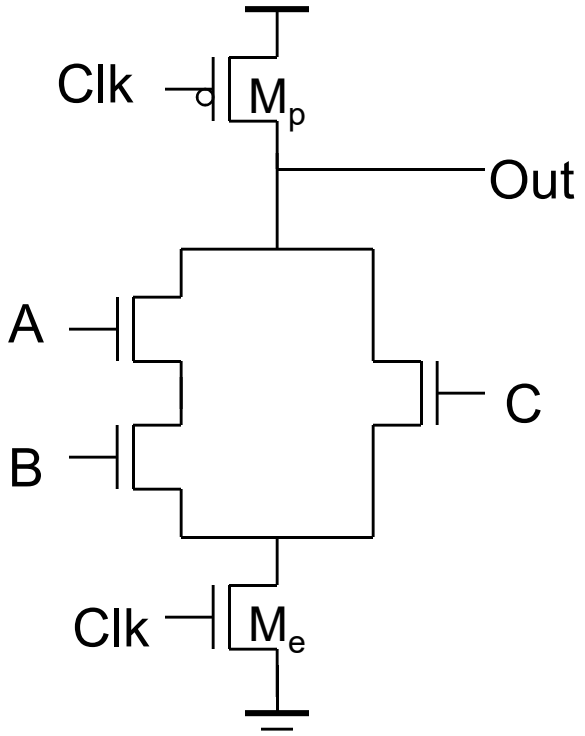

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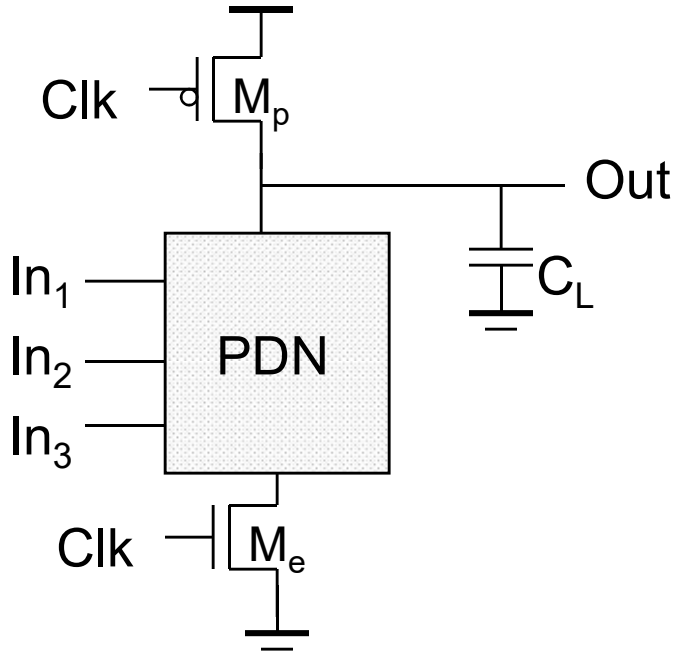

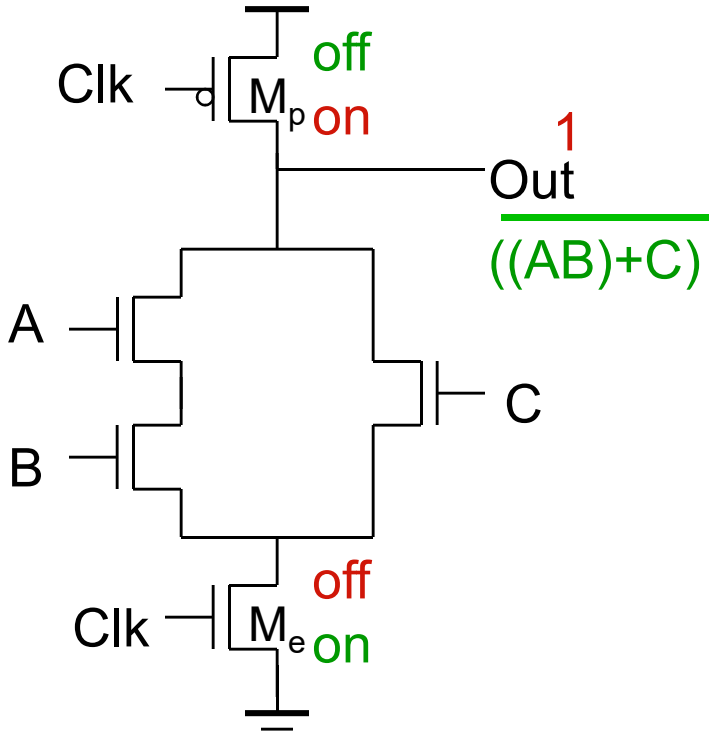

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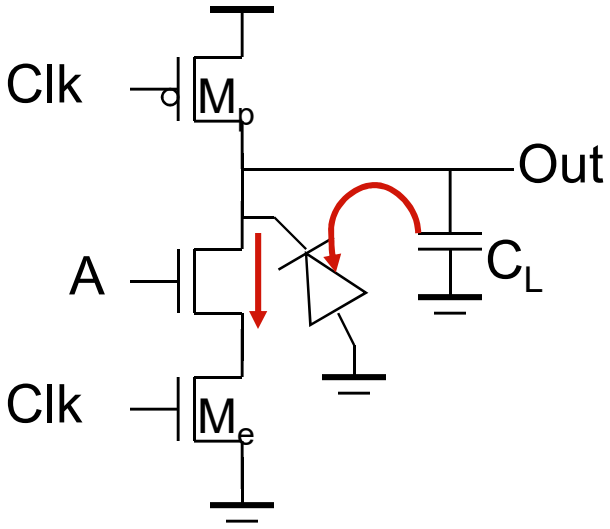

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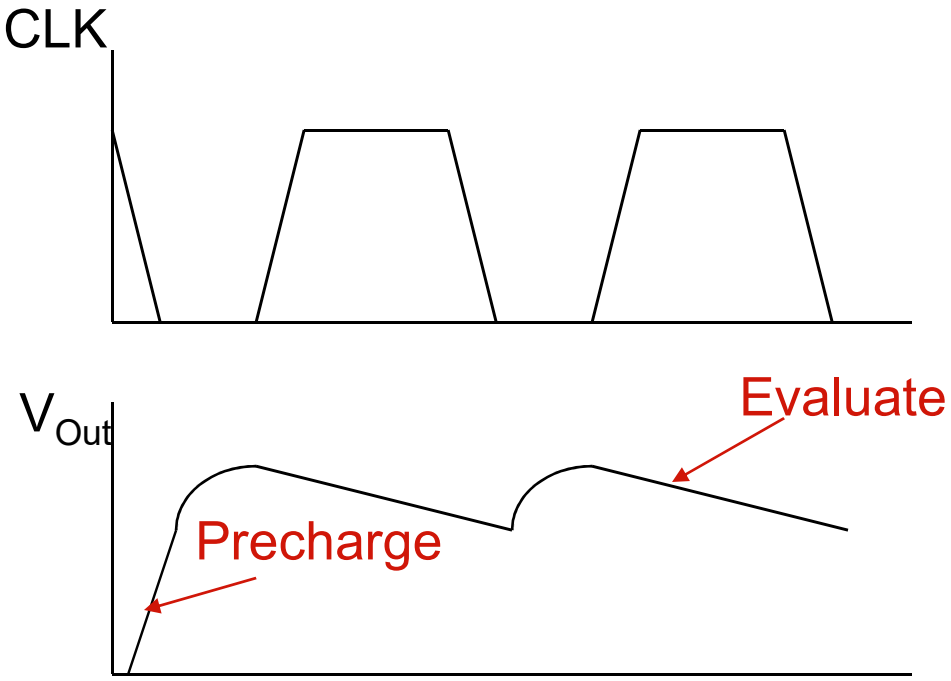

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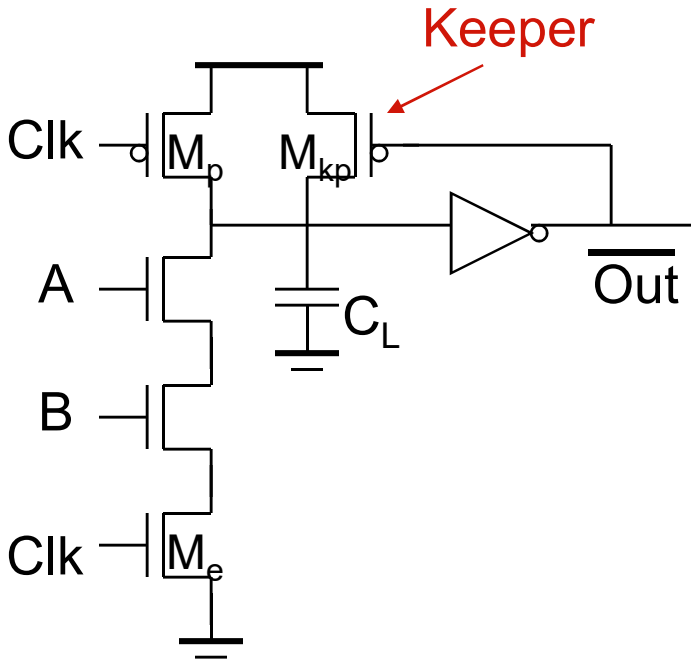

Same approach as level restorer for pass-transistor logic

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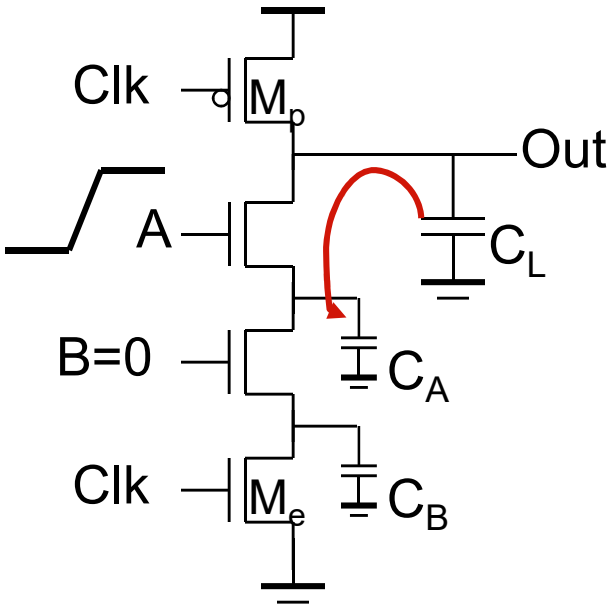

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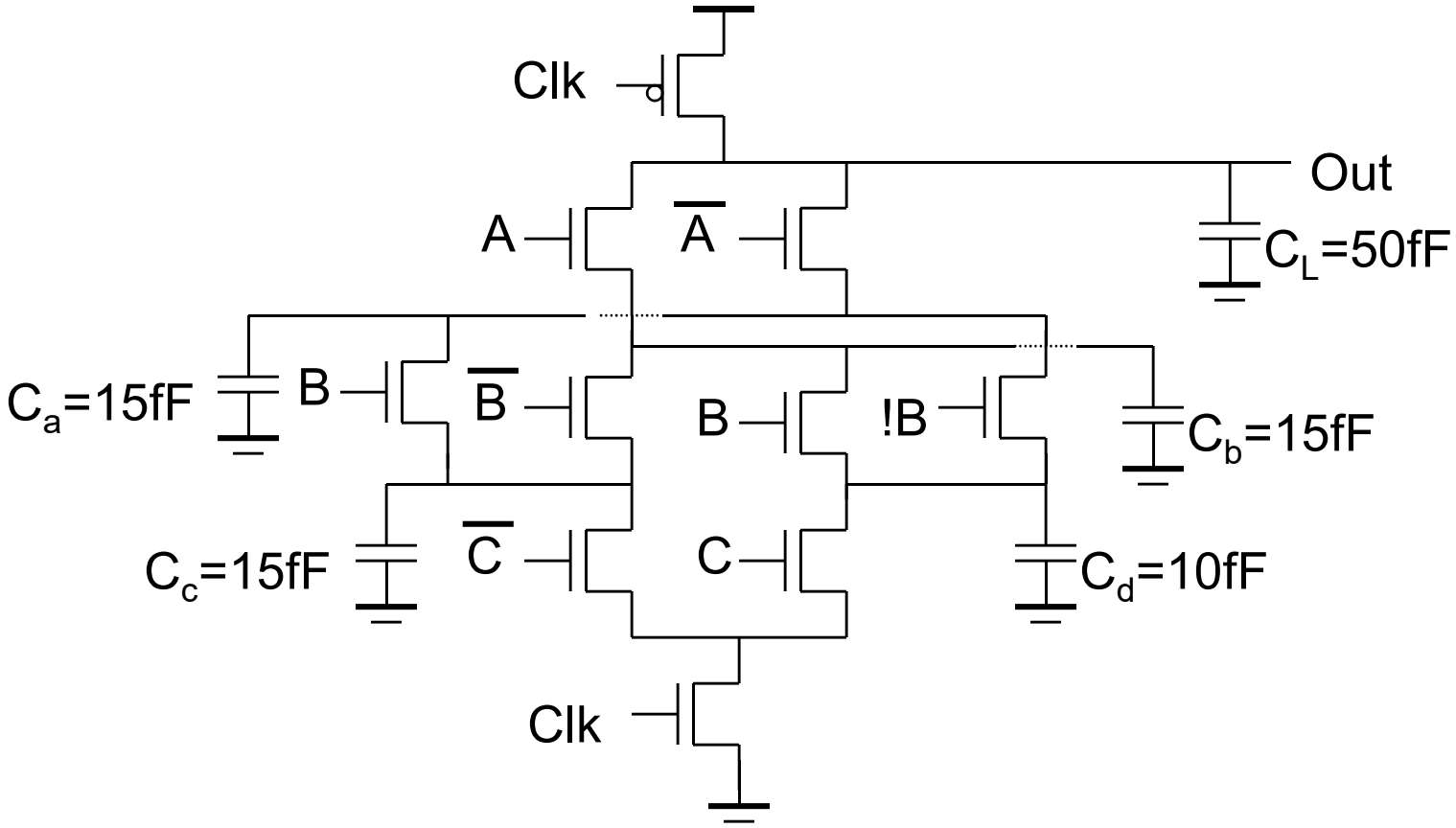

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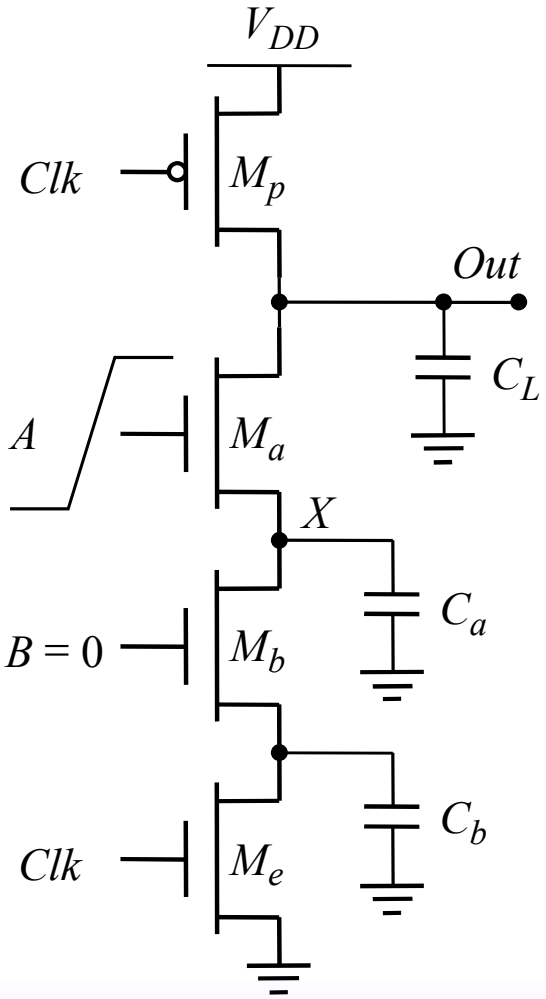

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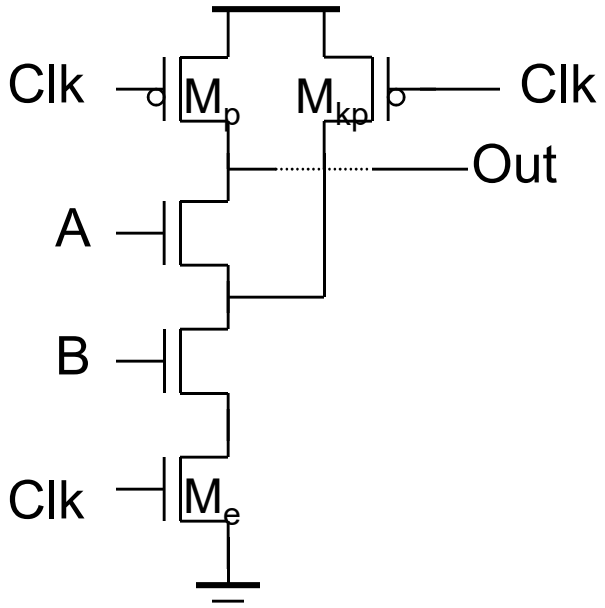

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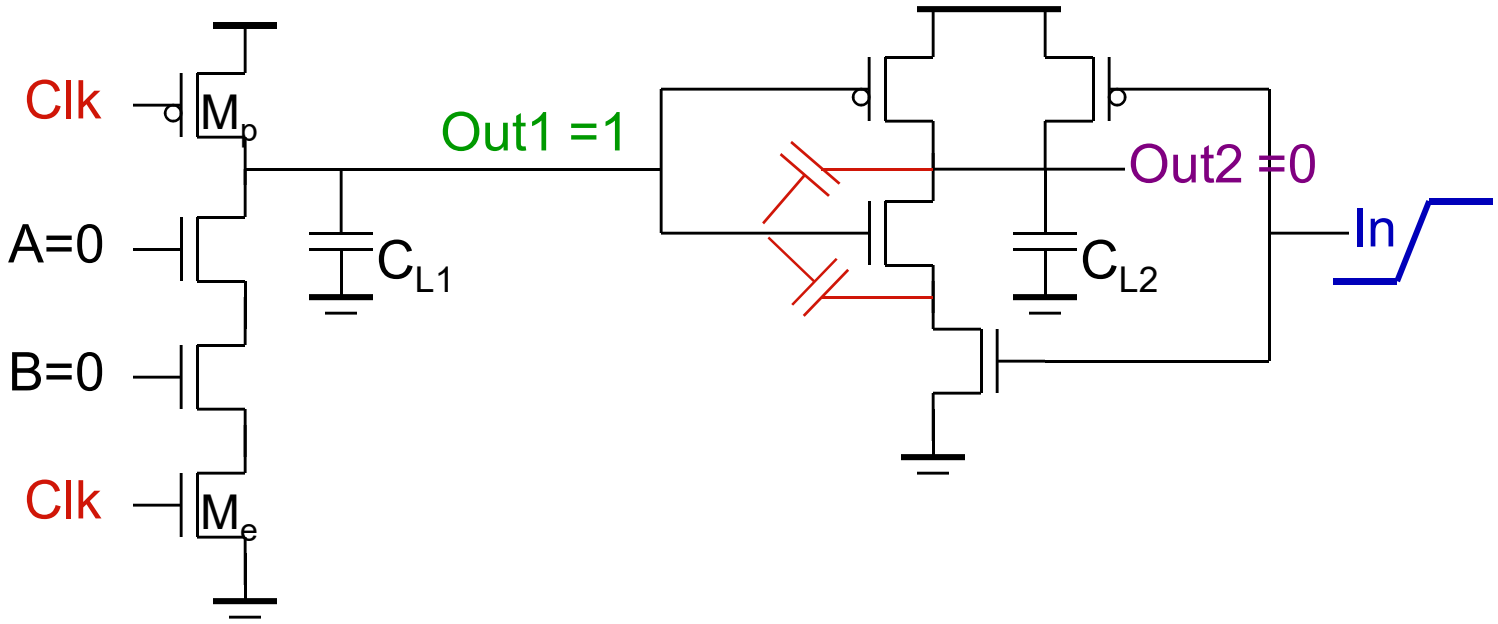

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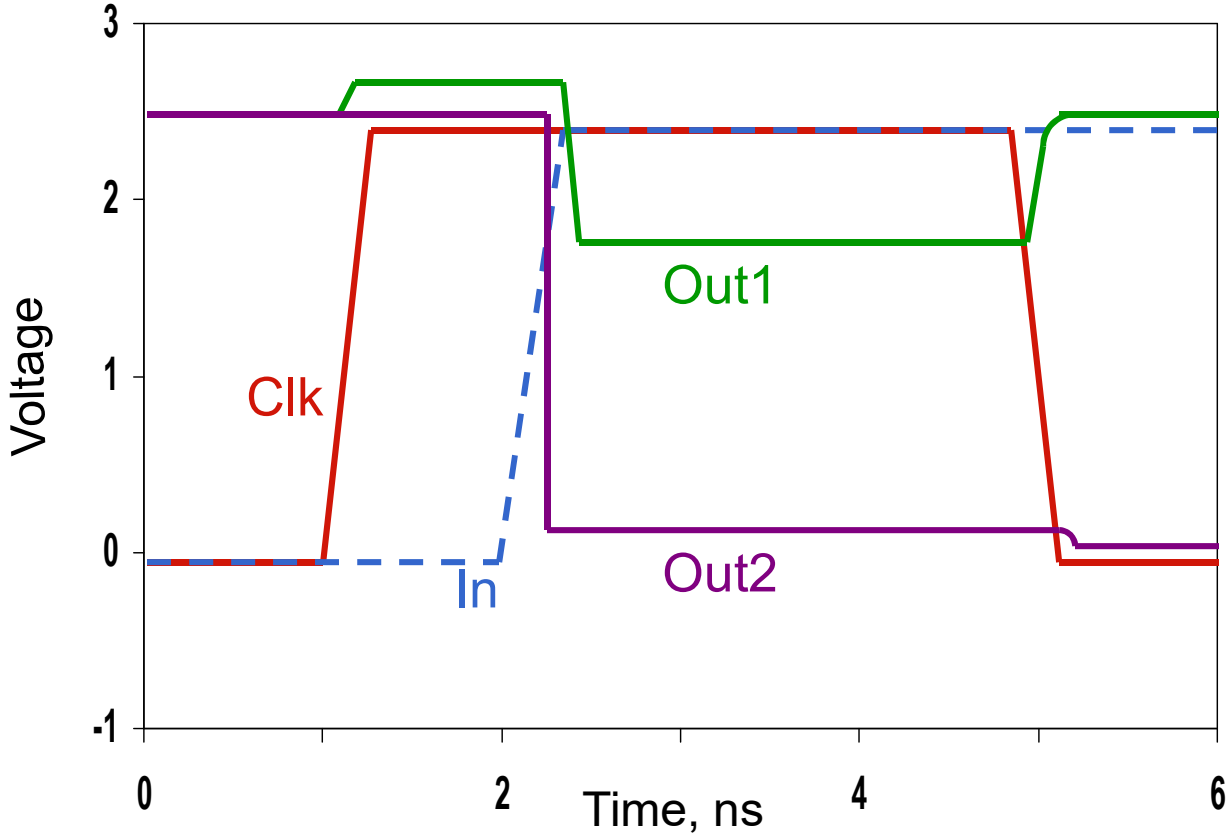

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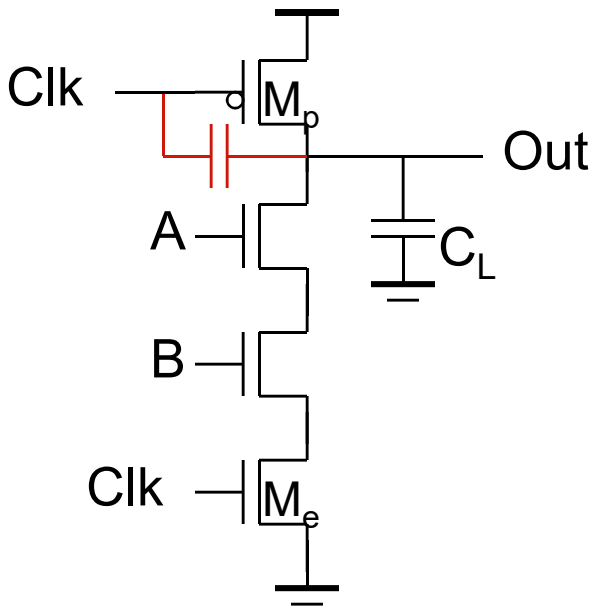

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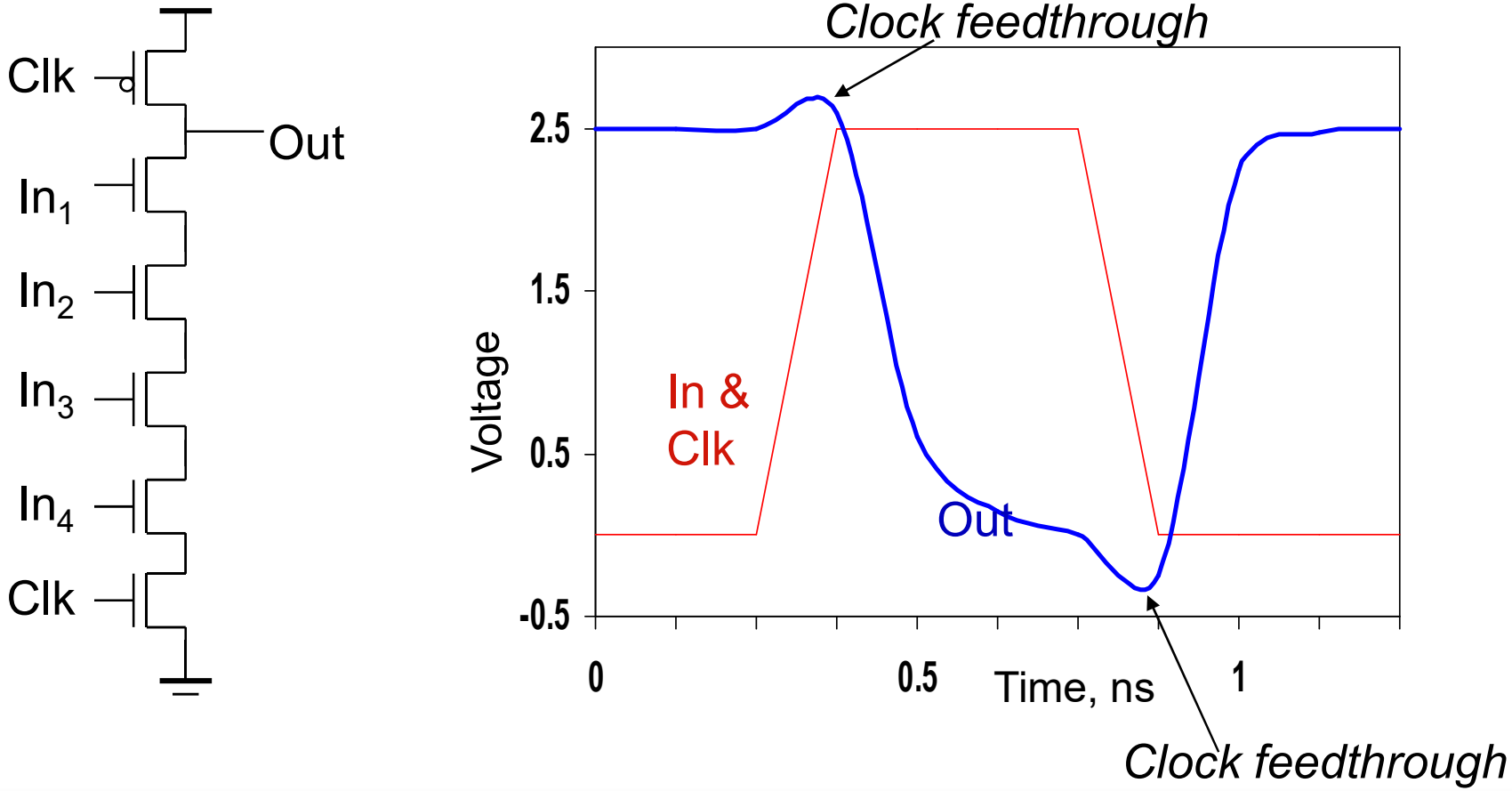

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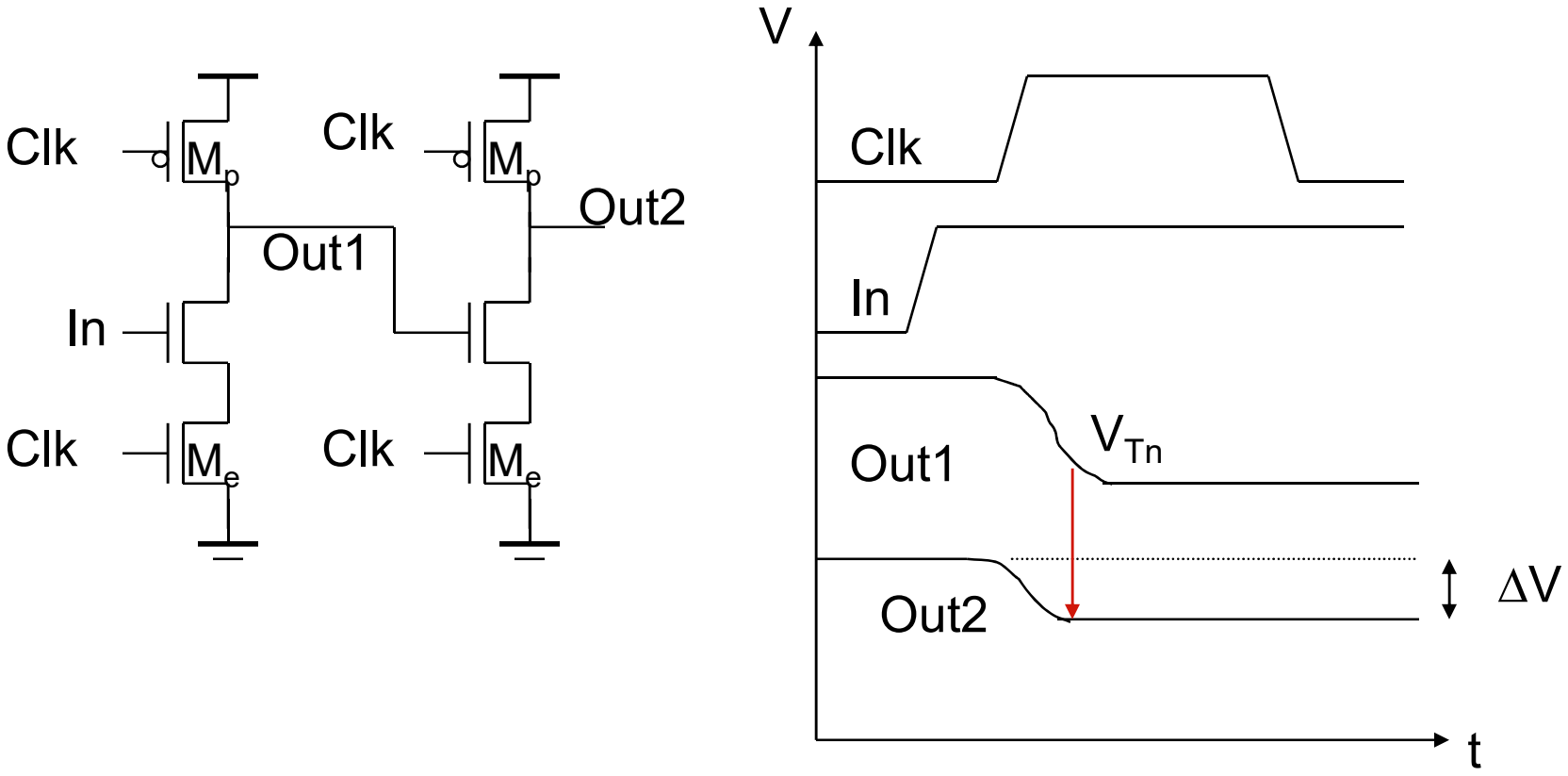

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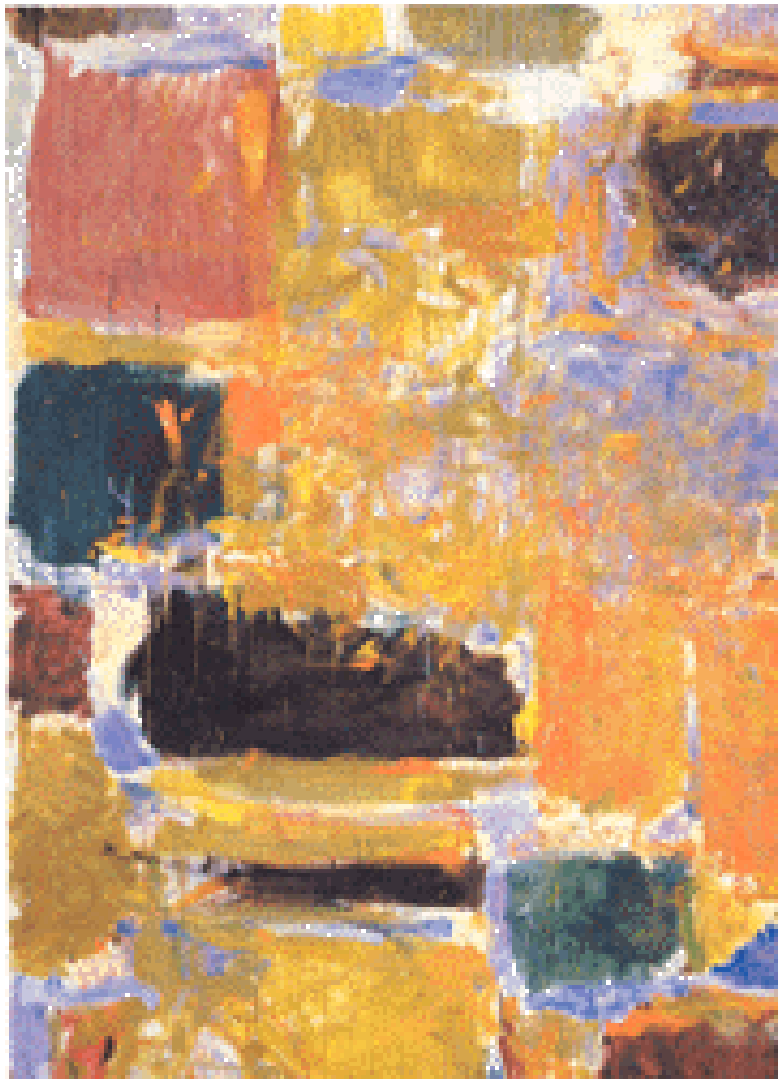

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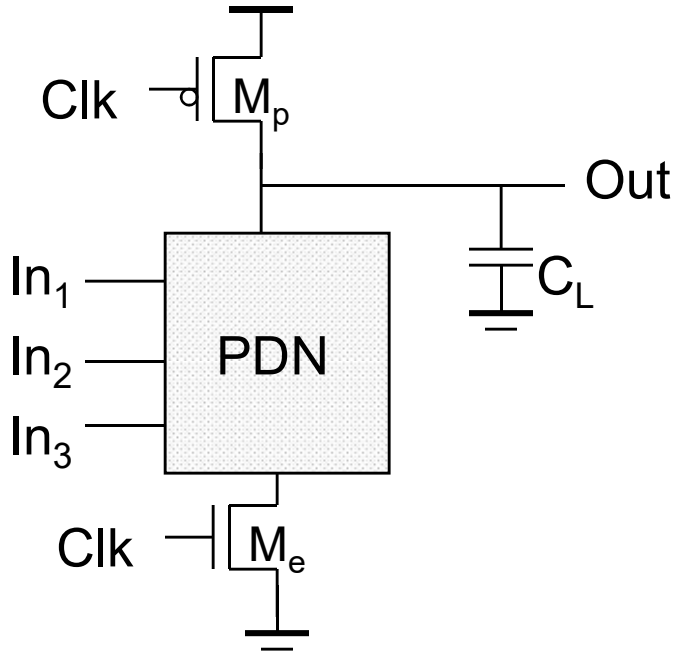

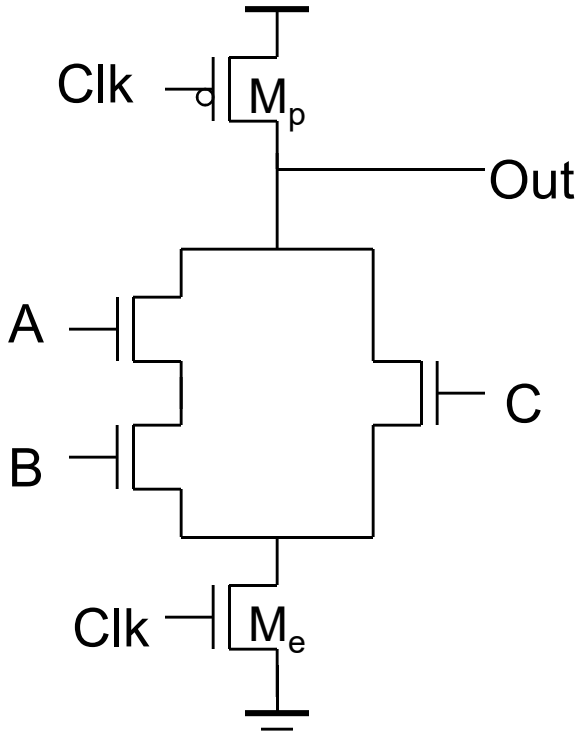

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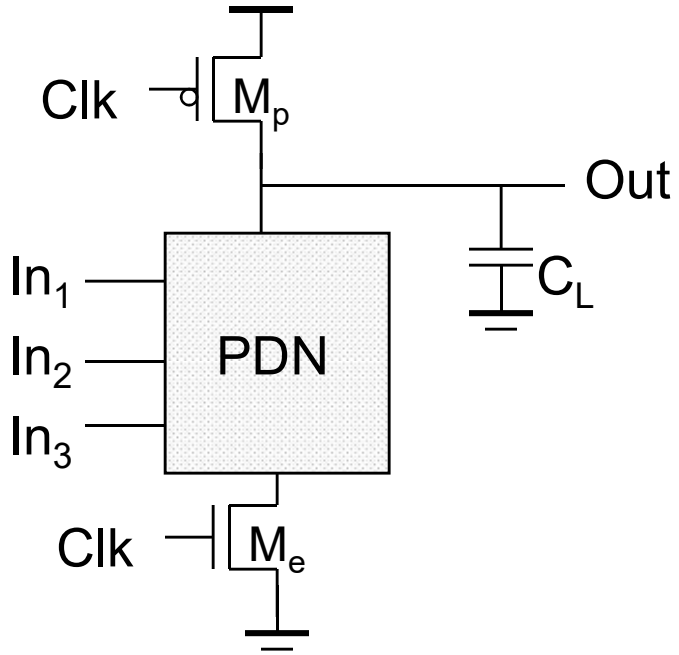

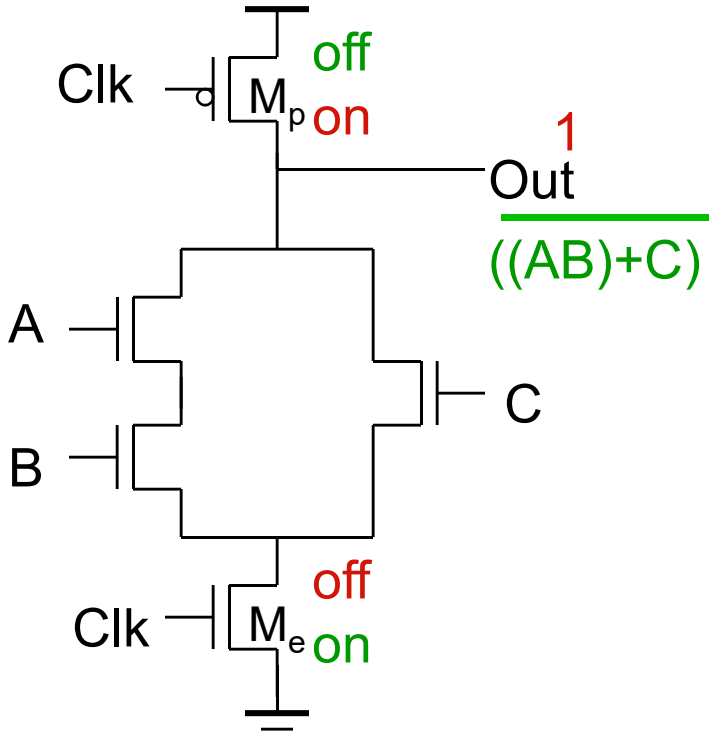

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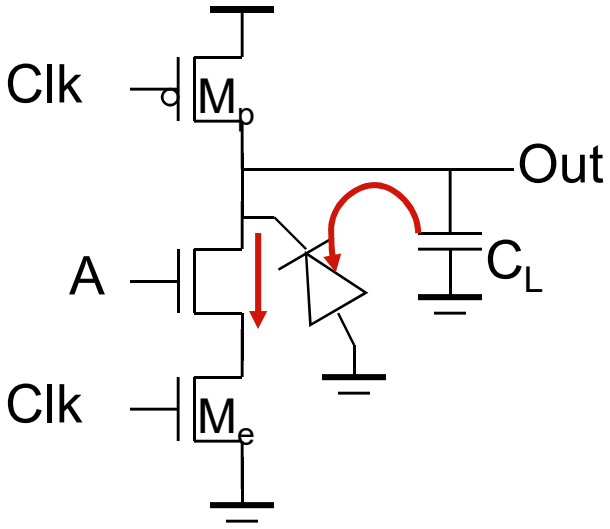

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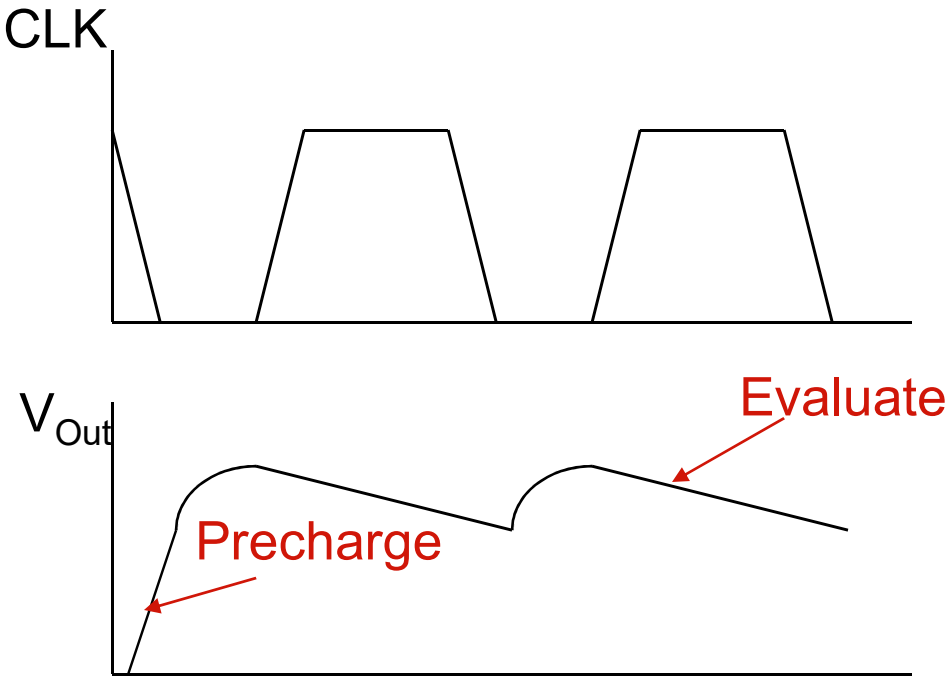

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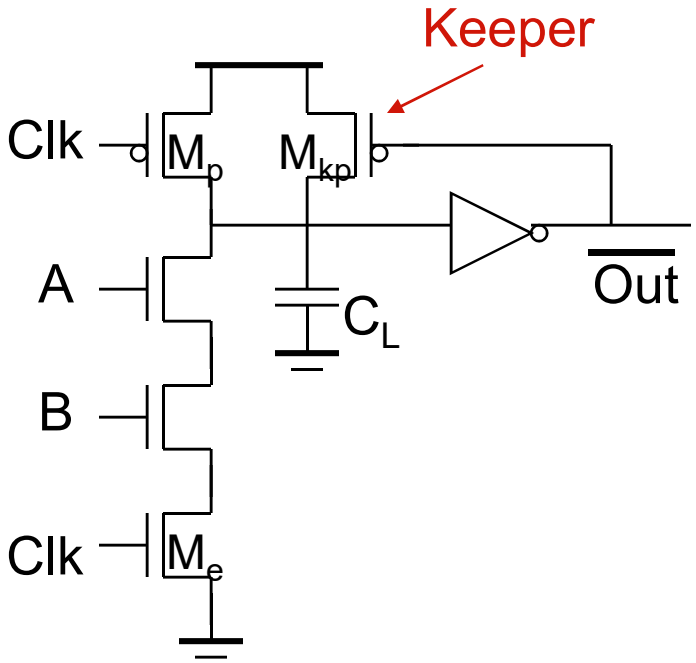

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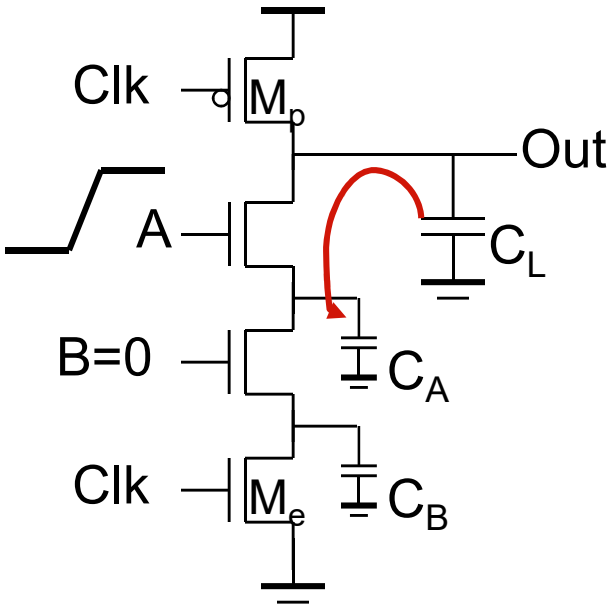

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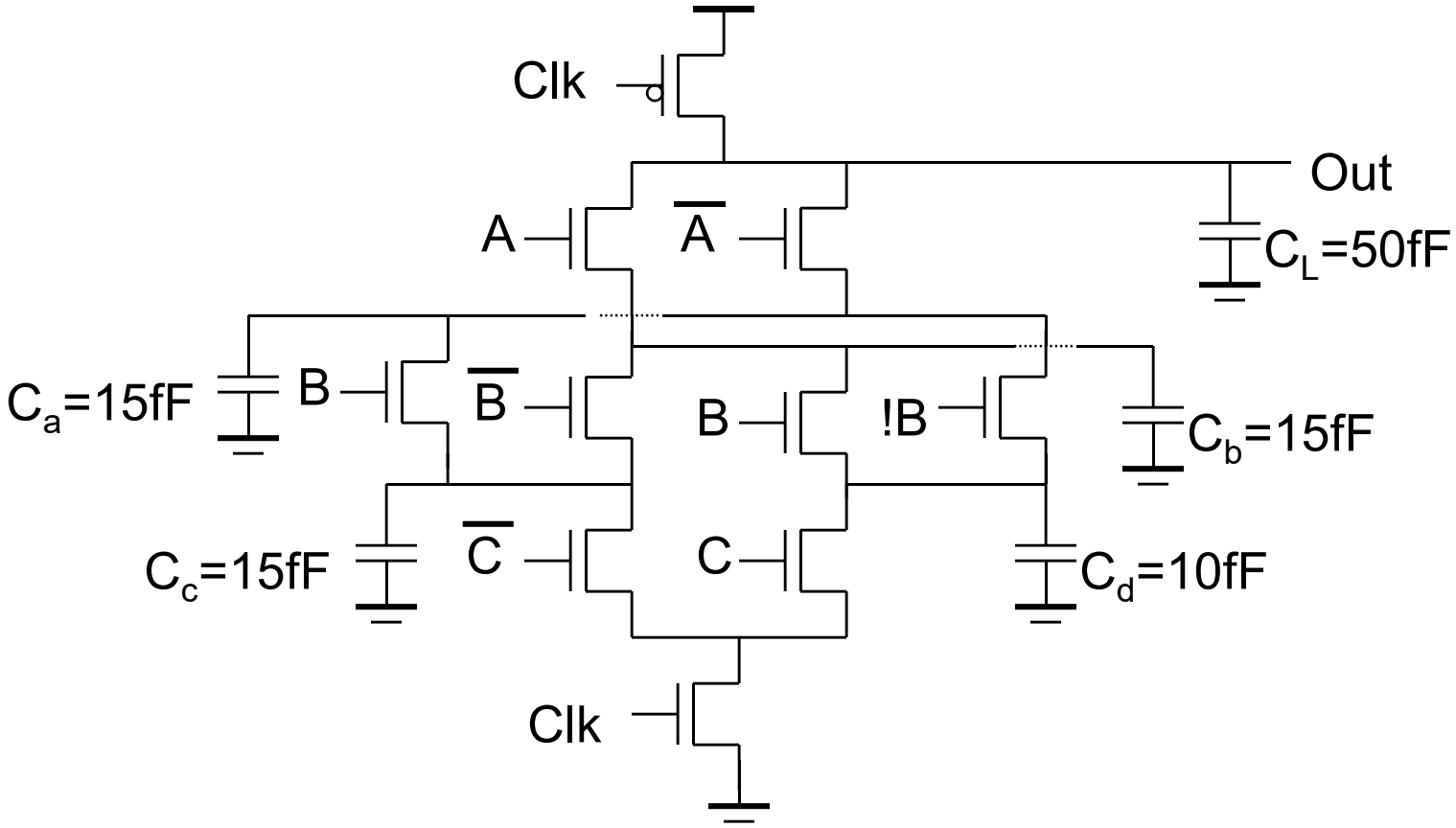

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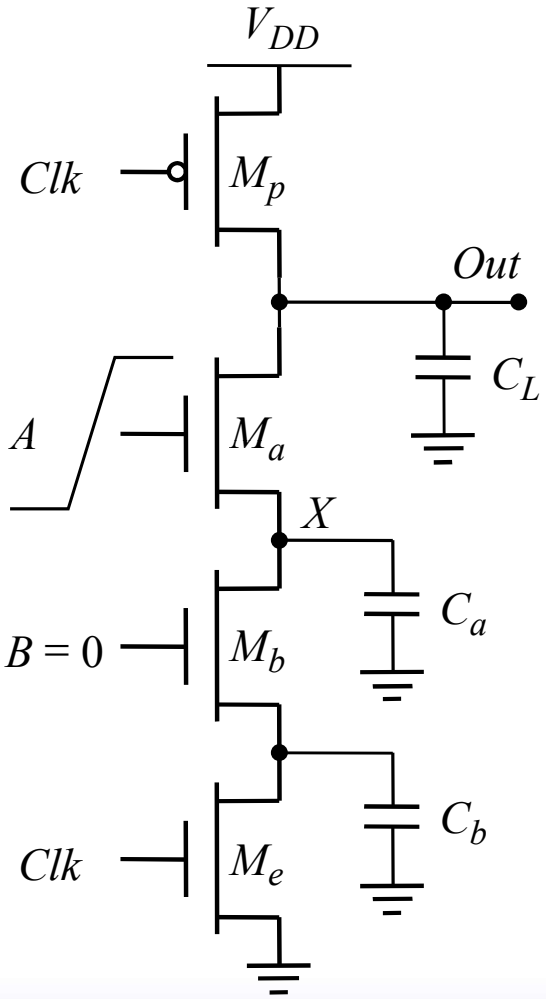

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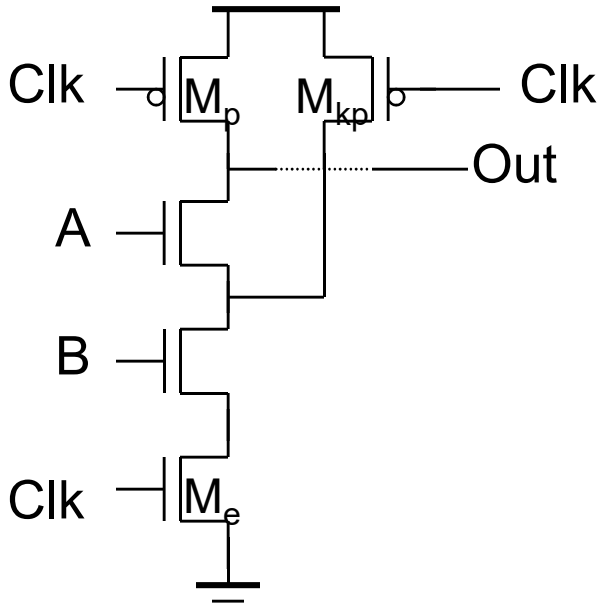

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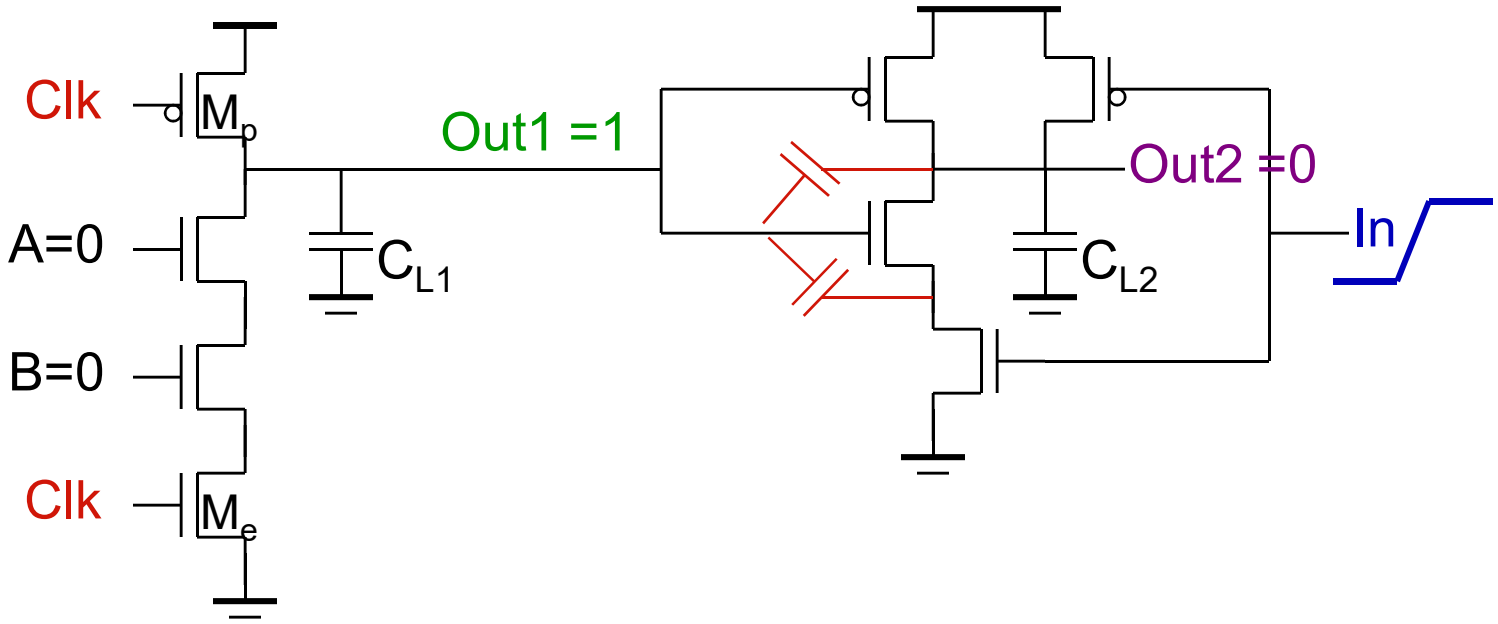

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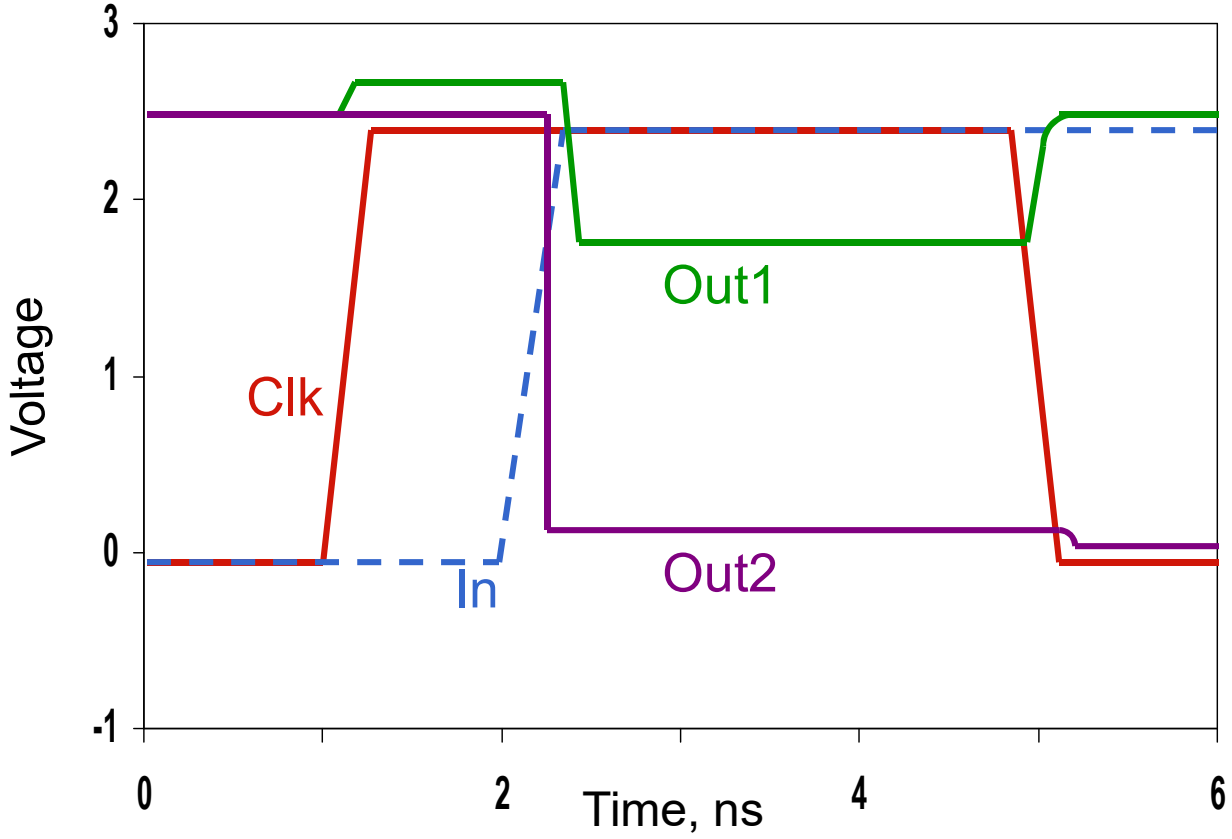

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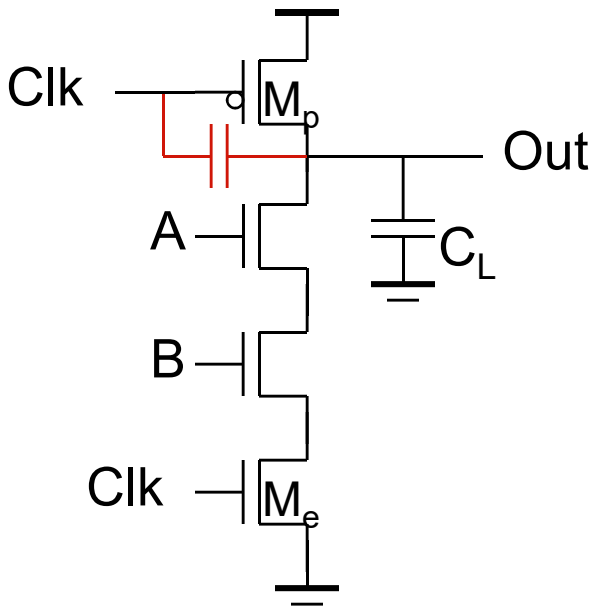

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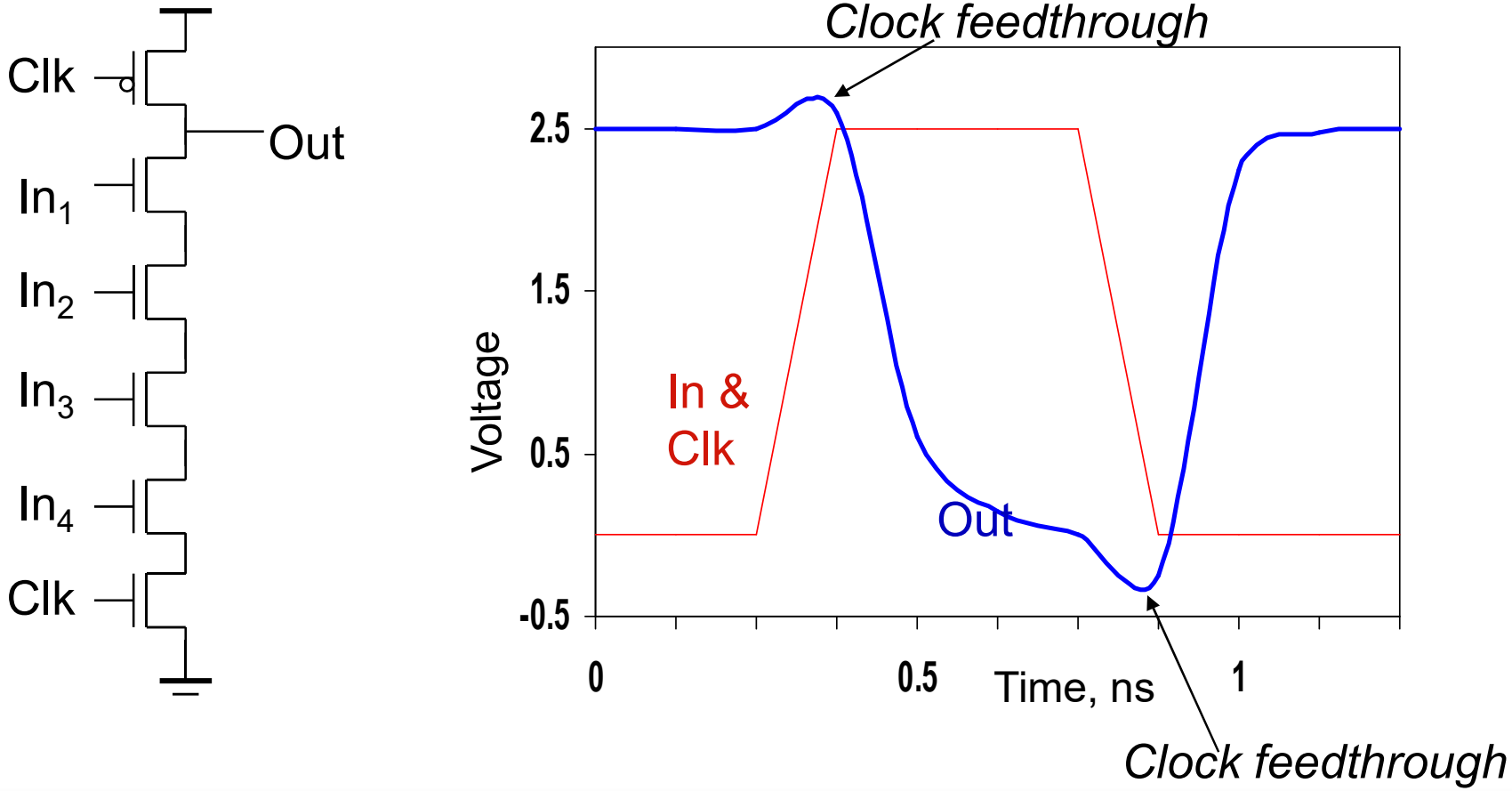

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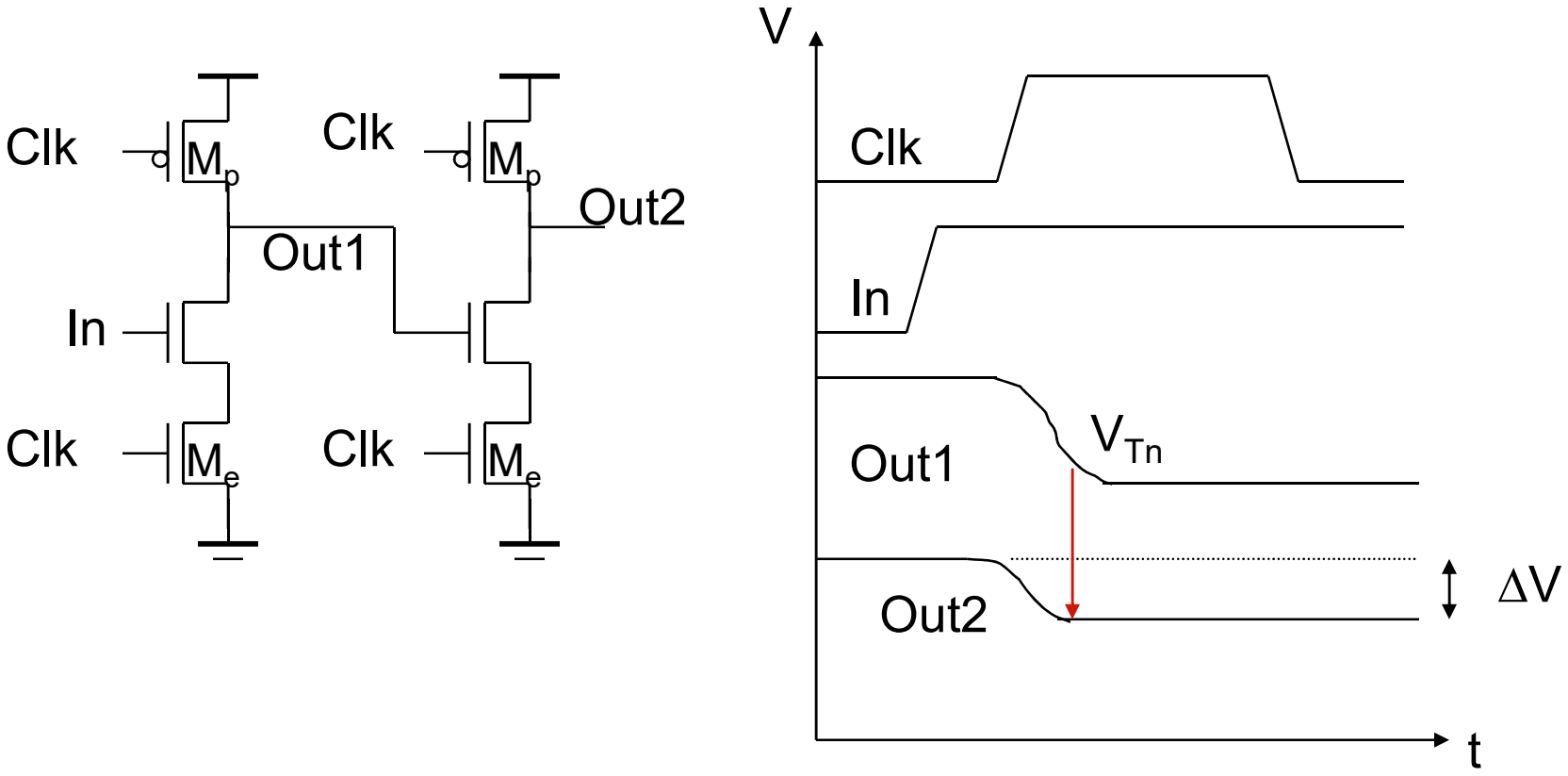

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